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Transistors

2SB0621A

Silicon PNP epitaxial planar type

For low-frequency driver amplification Complementary to 2SD0592A

■ Features

- ullet Low collector-emitter saturation voltage $V_{\text{CE(sat)}}$
- ullet High transition frequency f_T

\blacksquare Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V _{CBO}	-60	V	
Collector-emitter voltage (Base open)	V _{CEO}	-50	V	
Emitter-base voltage (Collector open)	V _{EBO}	-5	V	
Collector current	I_{C}	-1	A	
Peak collector current	I_{CP}	-1.5	A	
Collector power dissipation	P _C	750	mW	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C ,	

■ Package

• Code

TO-92B-B1

- Pin Name
 - 1. Emitter
 - 2. Collector
 - 3. Base

■ Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_{\rm C} = -10 \mu\text{A}, I_{\rm E} = 0$	-60	10		V
Collector-emitter voltage (Base open)	V _{CEO}	$I_{\rm C} = -2 \text{ mA}, I_{\rm B} = 0$	-50	$O_{(I)}$		V
Emitter-base voltage (Collector open)	$V_{\rm EBO}$	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -20 \text{ V}, I_E = 0$	80		-0.1	μΑ
Forward current transfer ratio	h _{FE1} *	$V_{CE} = -10 \text{ V}, I_{C} = -500 \text{ mA}$	85		340	
	h _{FE2}	$V_{CE} = -5 \text{ V}, I_{C} = -1 \text{ A}$	50			
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		-0.2	-0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = -500 \text{ mA}, I_B = -50 \text{ mA}$		-0.85	-1.2	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 50 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance (Common base, input open circuited)	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		20	30	pF

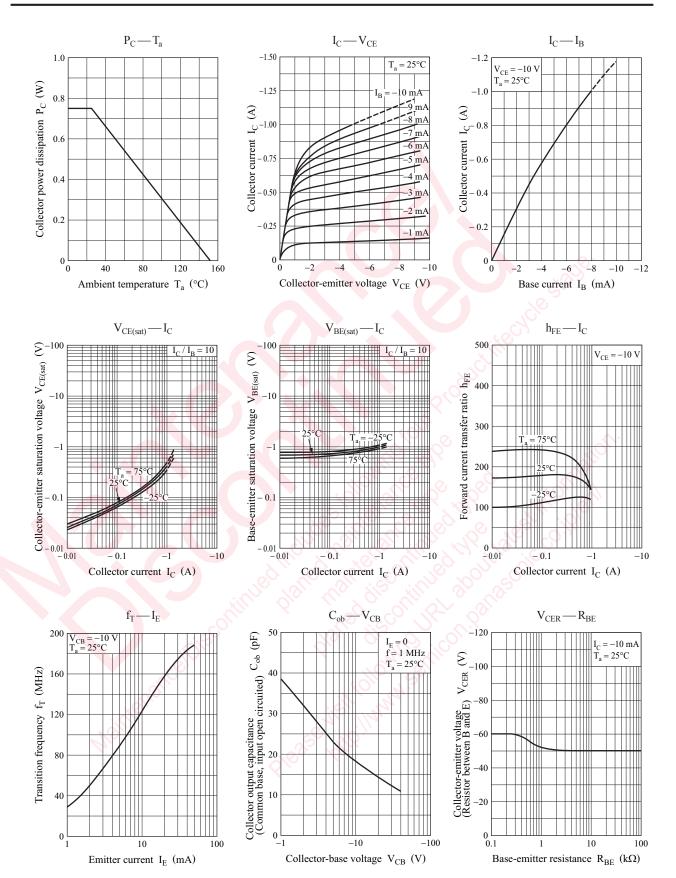
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	Q	R	S	
h_{FE1}	85 to 170	120 to 240	170 to 340	

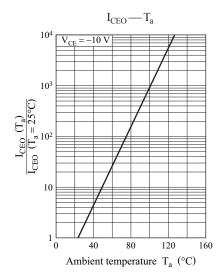
2SB0621A

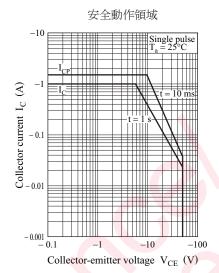
Panasonic



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Panasonic 2SB0621A

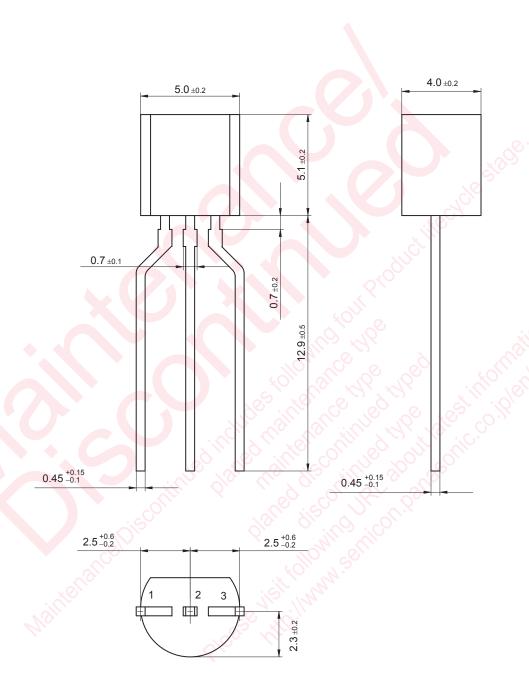




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2SB0621A Panasonic

TO-92-B1 Unit: mm



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